

Supporting Information

**Passivation of Surface States by ALD-Grown TiO<sub>2</sub> Overlayers  
on Ta<sub>3</sub>N<sub>5</sub> Anodes for Photoelectrochemical Water Oxidation**

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## Experimental Section

### Preparation of Ta<sub>3</sub>N<sub>5</sub> thin film photoanode

Ta foil (99.5%, Beijing Sunstone Tungsten Molybdenum Co., Ltd.) was first annealed in a tube furnace under the flow of air at 600 °C for 30 min. Then the obtained Ta<sub>2</sub>O<sub>5</sub> film was annealed in the tube furnace under the flow of NH<sub>3</sub> at 850 °C for 8 h. After the annealing, the surface of the obtained Ta<sub>3</sub>N<sub>5</sub> thin film photoanode was cleaned with N<sub>2</sub> flow.

*Atomic layer deposition (ALD) of TiO<sub>2</sub> overlayer:* TiO<sub>2</sub> overlayer was deposited onto Ta<sub>3</sub>N<sub>5</sub> thin film photoanode at 250 °C in a home-made ALD system using titanium (IV) isopropoxide (TTIP, 99.99%, Sigma-Aldrich Co. LLC.) and H<sub>2</sub>O as precursors. The precursors were held at 55 °C and 25 °C respectively. One ALD cycle consists of TTIP dose for 0.06 s, N<sub>2</sub> purge for 10 s, H<sub>2</sub>O dose for 0.2 s and N<sub>2</sub> purge for 10 s.

### Characterization

The morphology and microstructure of the samples were characterized by field-emission scanning electron microscopy (S-4800, Hitachi). The crystal structure of the sample was investigated using an X-ray diffractometer (D/MAX-2500) with Cu K $\alpha$  radiation ( $\lambda$  = 1.5416 Å) at 40 kV and 140 mA. X-ray photoelectron spectroscopy (XPS) analysis of the samples was carried out on a Physical Electronics PHI 1600 ESCA system with an Al K $\alpha$  X-ray source (E = 1486.6 eV). The binding energy was calibrated using the C 1s photoelectron peak at 284.6 eV as the reference. The thickness of the TiO<sub>2</sub> overlayer was characterized by an M-2000 DI spectroscopic ellipsometer (J.A. Woollam Co., Inc.).

### Electrochemical measurements

Electrochemical measurements of Ta<sub>3</sub>N<sub>5</sub> NTAs electrodes were performed using a three-electrode configuration with the Ta<sub>3</sub>N<sub>5</sub> NTAs as the working electrode; saturated Ag/AgCl as the reference electrode; and platinum foil (2 × 2 cm<sup>2</sup>) as the counter electrode. A 1.0 M

NaOH (99% Tianjin Windship Chemistry Technological Co.) aqueous solution (pH 13.6) was used as the electrolyte which was purged with N<sub>2</sub> for 20 min to remove the oxygen before the measurements. Potentials *vs.* Ag/AgCl were converted into potentials *vs.* RHE according to the Nernst equation ( $E_{\text{RHE}} = E_{\text{Ag/AgCl}} + 0.059\text{pH} + 0.196$ ). An electrochemical workstation (CompactStat.e20250, IVIUM) was used to measure the *J–V* curves and EIS. The *J–V* curves were measured with a scan rate of 20 mV s<sup>−1</sup> under the irradiation of a 300 W xenon lamp (Beijing Perfectlight Technology Co. Lt, LS-SXE300CUV) equipped with an AM1.5G filter. The intensity of the light was adjusted to 100 mW cm<sup>−2</sup>. Before the test, the electrode was encapsulated by epoxy and covered with a mask to expose 0.28 cm<sup>2</sup> surface area to the irradiation. EIS data were gathered at a bias of 1.0 V *vs.* RHE using a 25 mV amplitude perturbation of between 10,000 and 0.1 Hz under irradiation. Data were fitted using Zview software (Scribner Associates).